

AMENDMENT TO THE TITLE

Please amend the title as follows:

~~HIGHLY CONDUCTIVE SEMICONDUCTOR STRUCTURES, A
METHOD OF FORMING SAME~~ HIGHLY CONDUCTIVE
SEMICONDUCTOR STRUCTURES VIA PLASMA ETCH[[,]] ~~AND
ELECTRICAL DEVICES INCORPORATING HIGHLY CONDUCTIVE
SEMICONDUCTOR STRUCTURES~~

AMENDMENTS TO THE CLAIMS

1-26. (Cancelled)

27. (Withdrawn) A plasma, comprising chlorine atoms and oxygen atoms at a pressure of between about 2 mTorr and about 4 mTorr, wherein said plasma is formed by a decoupled plasma source.

28. (Withdrawn) The plasma of claim 27, wherein said decoupled plasma source has a flux source power of about 800 watts to about 1500 watts and a plasma bias power of about 50 watts to about 150 watts.

29. (Withdrawn) A method of making a plasma, comprising feeding gases comprising chlorine and oxygen to a decoupled plasma source, and wherein the plasma is produced at a pressure of between about 2 mTorr and about 4 mTorr.

30. (Withdrawn) The method of Claim 29, wherein chlorine is provided at a flow rate of between about 40 and about 100 sccm, and oxygen is provided at a flow rate of about 4 to about 12 sccm.

31. (Withdrawn) The method of claim 29, wherein said decoupled plasma source has a flux source power of about 800 watts to about 1500 watts and a plasma bias power of about 50 watts to about 150 watts.

32. (Withdrawn) The method of claim 30, wherein said decoupled plasma source has a flux power source of about 800 watts to about 1500 watts and a plasma bias power of about 50, watts to about 150 watts.

33. (Withdrawn) A method of etching, comprising etching with the plasma produced by the process of claim 29.

34. (Withdrawn) A method of etching, comprising etching with the plasma produced by the process of claim 32.

35. (Currently Amended) A process for making a semiconductor structure comprising:

depositing a conductive layer upon a substrate comprising a silicon oxide-silicon nitride-silicon oxide (ONO) layer;

depositing a conductive adhesive layer comprising polysilicon between said substrate and said conductive layer, wherein said conductive adhesive layer has a minimum thickness required to provide adhesion between said substrate and said conductive layer for a robust structure that can withstand subsequent processing, wherein said conductive adhesive layer has a thickness that is less than 300 greater than 10 and less than or equal to 100 angstroms; and

etching a portion of said conductive layer and a portion of said conductive adhesive layer utilizing a plasma without sacrificing said substrate, wherein said plasma comprises an etchant, wherein said etchant comprises chlorine and oxygen,

wherein said plasma is ionized and sustained by a first RF source, and wherein said plasma is accelerated by a second RF source, wherein said etching is conducted at a pressure of between 2 mTorr and 4 mTorr, wherein a selectivity of said etching obviates a need for an adhesive layer of greater than 100 angstrom thickness, and wherein said process yields a semiconductor structure comprising a lower electrical resistance and a shorter vertical profile than a semiconductor structure comprising a conductive adhesive layer of greater than 100 angstrom thickness.

36. (Cancelled)

37. (Previously Presented) The process of Claim 36, wherein said conductive layer and said conductive adhesive layer have a combined thickness of approximately 3000 angstroms or less.

38. (Previously Presented) The process of Claim 35, wherein [[:]]
~~said conductive adhesive layer comprises polysilicon; and~~
said conductive layer comprises a material selected from the group consisting of tungsten and tungsten silicide.

39. (Cancelled)

40. (Previously Presented) The process of Claim 35, wherein a flow rate of said chlorine is approximately 40 to 100 sccm.

41. (Previously Presented) The process of Claim 35, wherein a flow rate of said oxygen is approximately 4 to 12 sccm.

42. (Previously Presented) The process of Claim 35, wherein said first RF source is approximately 800 to 1500 watts.

43. (Previously Presented) The process of Claim 35, wherein said second RF source is approximately 50 to 150 watts.

44-55. (Cancelled)